

Application Serial No. 10/615,899  
Reply to office action of April 6, 2006

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PATENT  
Docket: CU-3282

**Amendments to the Claims**

The listing of claims presented below will replace all prior versions, and listings, of claims in the application.

**Listing of claims:**

1. (Previously presented) A method for improving reliability of an etching apparatus and a deposition apparatus, which etching and deposition apparatus' use chlorine-containing etching and deposition gases respectively, the method comprising the steps of:

generating a plasma in the apparatus that includes hydrogen and nitrogen and 5% to 90% argon in the reaction unit to remove a residual remaining in a reaction tube of the reaction unit.

2-10. (Cancelled)

11. (Previously presented) A method for improving reliability of an etching apparatus and a deposition apparatus, which etching and deposition apparatus' use chlorine-containing etching and deposition gases respectively, the method comprising the steps of:

generating a plasma in the apparatus that includes nitrogen and 5% to 90% hydrogen in the reaction unit to remove a residual remaining in a reaction tube of the reaction unit.

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12. (Previously presented) A method for improving reliability of an etching apparatus and a deposition apparatus, which etching and deposition apparatus' use chlorine-containing etching and deposition gases respectively, the method comprising the steps of:

generating a plasma in the apparatus that includes hydrogen and nitrogen in the reaction unit to remove a residual remaining in a reaction tube of the reaction unit, wherein the plasma including nitrogen comprises hydrogen of 5 to 50% and argon of 5 to 90%.